EMICO					
		1N3595			
Small	Signal Diode	DO-35 Color Band Denotes Cathode			
	e Maximum Ratings*	$T_A = 25^{\circ}C$ unless otherwise noted			
Symbol	Para	ameter	Value		Units
V _{RRM}	Maximum Repetitive Reverse Vo	ximum Repetitive Reverse Voltage 150			V
I _{F(AV)}	Average Rectified Forward Curre	ent	200		mA
I _{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond				A A
T _{stg}	Storage Temperature Range			00	°C
-					-
OTES:	Operating Junction Temperature e limiting values above which the serviceability or re based on a maximum junction temperature of	f any semiconductor device may be impaired.	175		°C ℃
These ratings ar OTES : These ratings a These are stear Thermal Symbol P _D R _{0JA}	e limiting values above which the serviceability or re based on a maximum junction temperature of dy state limits. The factory should be consulted or Characteristics Para Power Dissipation Thermal Resistance, Junction to	f any semiconductor device may be impaired. 200 degrees C. n applications involving pulsed or low duty cycle opera ameter Ambient			-
These ratings ar DTES: These ratings a These are stear Thermal Symbol P _D R _{6JA}	e limiting values above which the serviceability or re based on a maximum junction temperature of dy state limits. The factory should be consulted or Characteristics Para Power Dissipation Thermal Resistance, Junction to	f any semiconductor device may be impaired. 200 degrees C. n applications involving pulsed or low duty cycle opera	ations. Value 500		°C Units mW
These ratings ar DTES: These ratings a These are stear Thermal Symbol P _D R _{6JA}	e limiting values above which the serviceability or re based on a maximum junction temperature of dy state limits. The factory should be consulted on Characteristics Para Power Dissipation Thermal Resistance, Junction to al Characteristics	f any semiconductor device may be impaired. 200 degrees C. n applications involving pulsed or low duty cycle opera ameter Ambient 5°C unless otherwise noted	ations. Value 500 300	· · · · · · · · · · · · · · · · · · ·	°C Units mW °C/W
These ratings ar DTES: These ratings a These are stear Thermal Symbol P _D R _{0JA}	e limiting values above which the serviceability or re based on a maximum junction temperature of dy state limits. The factory should be consulted or Characteristics Para Power Dissipation Thermal Resistance, Junction to al Characteristics $T_A = 2$ Parameter	f any semiconductor device may be impaired. 200 degrees C. n applications involving pulsed or low duty cycle opera ameter Ambient 5°C unless otherwise noted Test Conditions $I_R = 100 \ \mu A$ $I_F = 1.0 \ m A$ $I_F = 5.0 \ m A$ $I_F = 50 \ m A$ $I_F = 100 \ m A$ $I_F = 100 \ m A$ $I_F = 100 \ m A$	ations. Value 500 300 Min 150 0.52 0.60 0.65 0.75 0.79	Max 0.68 0.75 0.80 0.88 0.92	°C Units mW °C/W C/W Units V V V V V V V V V V
These ratings ar ores : These ratings a These ratings a These are stear Thermal Symbol P _D R _{0JA} Electrica Symbol V _R	e limiting values above which the serviceability or re based on a maximum junction temperature of dy state limits. The factory should be consulted on Characteristics Power Dissipation Thermal Resistance, Junction to al Characteristics $T_A = 2$ Parameter Breakdown Voltage	f any semiconductor device may be impaired. 200 degrees C. n applications involving pulsed or low duty cycle operations ameter Ambient 5°C unless otherwise noted Test Conditions $I_R = 100 \ \mu A$ $I_F = 1.0 \ m A$ $I_F = 5.0 \ m A$ $I_F = 5.0 \ m A$ $I_F = 50 \ m A$ $I_F = 100 \ m A$ $I_F = 200 \ m A$ $I_F = 125 \ V$ $V_R = 30 \ V, T_A = 125^{\circ}C$ $V_R = 125 \ V, T_A = 125^{\circ}C$	ations. Value 500 300 Min 150 0.52 0.60 0.65 0.75	Max 0.68 0.75 0.80 0.92 1.00 1 0.3 0.5	°С Units mW °С/W Units V V V V V V V V V V V V V
These ratings ar oTES: These ratings a These are stead Thermal Symbol P _D R _{0JA} Electrica Symbol V _R V _F	e limiting values above which the serviceability or re based on a maximum junction temperature of dy state limits. The factory should be consulted on Characteristics Power Dissipation Thermal Resistance, Junction to al Characteristics $T_A = 2$ Parameter Breakdown Voltage Forward Voltage	f any semiconductor device may be impaired. 200 degrees C. n applications involving pulsed or low duty cycle operations ameter Ambient 5°C unless otherwise noted Test Conditions I _R = 100 μ A I _F = 1.0 mA I _F = 5.0 mA I _F = 5.0 mA I _F = 50 mA I _F = 200 mA V _R = 125 V V _R = 30 V, T _A = 125°C	ations. Value 500 300 Min 150 0.52 0.60 0.65 0.75 0.79	Max 0.68 0.75 0.80 0.88 0.92 1.00 1 0.3	°C Units mW °C/W C/W Units V V V V V V V V V V V V V V V V V V

 $I_F = 10 \text{ mA}, V_R = -3.5 \text{ V},$ R_L = 1.0 kΩ

1N3595

t_{rr}

©2002 Fairchild Semiconductor Corporation

Reverse Recovery Time

1N3595, Rev. A

μs

3

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM BottomlessTM CoolFETTM CROSSVOLTTM DenseTrenchTM DOMETM EcoSPARKTM E²CMOSTM EnSignaTM FACTTM FACT Quiet SeriesTM FAST $^{\textcircled{(0)}}$ OPTOLFASTrTMOPTOFFRFETTMPACMAGlobalOptoisolatorTMPOPTMGTOTMPower2HiSeCTMPower7ISOPLANARTMQFETTMLittleFETTMQSTMMicroFETTMQT OptMicroPakTMQuiet SMICROWIRETMSILENT

OPTOLOGIC[™] OPTOPLANAR[™] PACMAN[™] POP[™] Power247[™] PowerTrench[®] QFET[™] QS[™] QT Optoelectronics[™] Quiet Series[™] SILENT SWITCHER[®] SMART START[™] VCX[™] STAR*POWER[™] SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-6 SuperSOT[™]-8 SyncFET[™] TinyLogic[™] TruTranslation[™] UHC[™] UltraFET[®]

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Product Status	Definition
Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
	Formative or In Design First Production Full Production